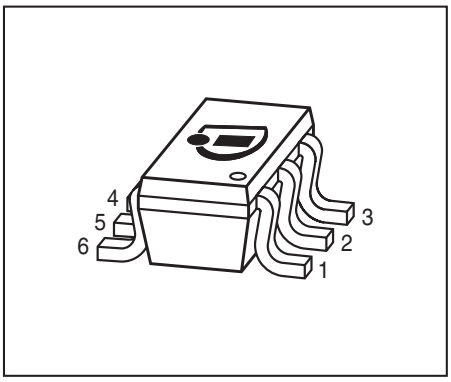
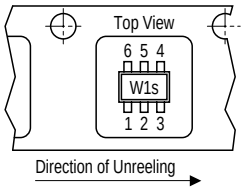
NPN / PNP Silicon AF Transistor Array



- High breakdown voltage
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated NPN/PNP Transistor in one package
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

AEC Qualified RoHS

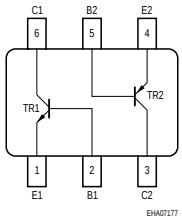
Tape loading orientation



Marking on SC74 package
(for example W1s)
corresponds to pin 1 of device

Position in tape: pin 1
opposite of feed hole side

SC74_Tape



Type	Marking	Pin Configuration						Package
SMBTA06UPN	s2P	1=E	2=B	3=C	4=E	5=B	6=C	SC74

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	80	V
Collector-base voltage	V_{CBO}	80	
Emitter-base voltage	V_{EBO}	4	
Collector current	I_C	500	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	1	A
Base current	I_B	100	mA
Peak base current	I_{BM}	200	
Total power dissipation- $T_S \leq 115$ °C	P_{tot}	330	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	≤ 105	K/W

Electrical Characteristics at T_A = 25°C, unless otherwise specified

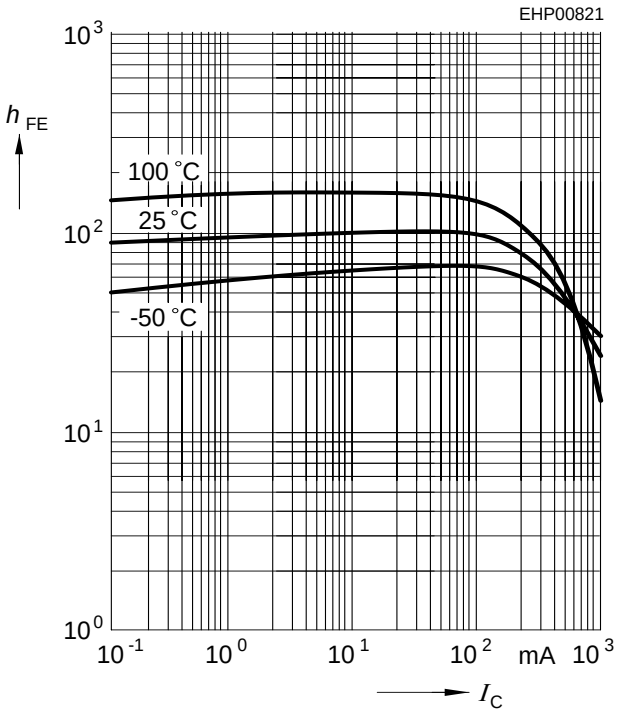
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	80	-	-	V
Collector-base breakdown voltage I_C = 100 µA, I_E = 0	$V_{(BR)CBO}$	80	-	-	
Emitter-base breakdown voltage I_E = 10 µA, I_C = 0	$V_{(BR)EBO}$	4	-	-	
Collector-base cutoff current	I_{CBO}				µA
V_{CB} = 80 V, I_E = 0		-	-	0.1	
V_{CB} = 80 V, I_E = 0 , T_A = 150 °C		-	-	20	
Collector-emitter cutoff current V_{CE} = 60 V, I_B = 0	I_{CEO}	-	-	100	nA
DC current gain[2)]	h_{FE}				-
I_C = 10 mA, V_{CE} = 1 V		100	-	-	
I_C = 100 mA, V_{CE} = 1 V		100	-	-	
Collector-emitter saturation voltage[2)] I_C = 100 mA, I_B = 10 mA	V_{CEsat}	-	-	0.25	V
Base-emitter voltage[2)] I_C = 100 mA, V_{CE} = 1 V	$V_{BE(ON)}$	-	-	1.2	
AC Characteristics					
Transition frequency I_C = 20 mA, V_{CE} = 5 V, f = 20 MHz	f_T	-	100	-	MHz
Collector-base capacitance V_{CB} = 10 V, f = 1 MHz	C_{cb}	-	7	-	pF

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

[2]Pulse test: t < 300µs; D < 2%

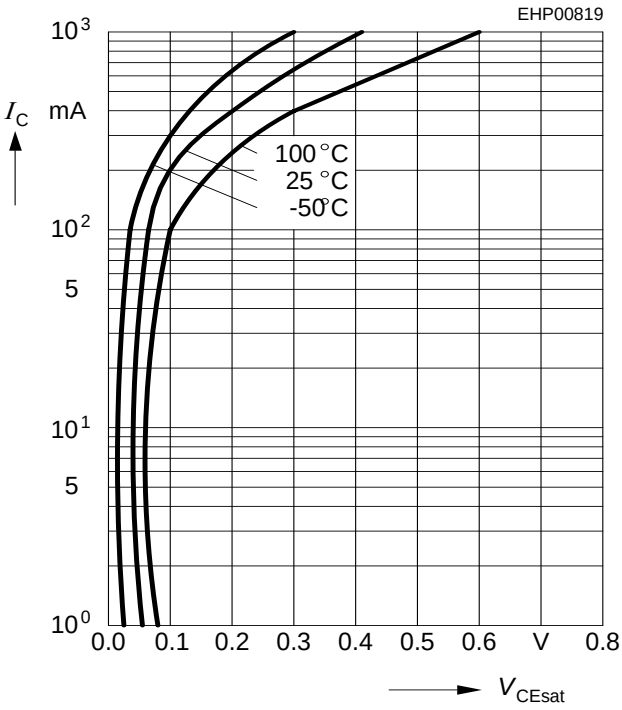
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 1 V



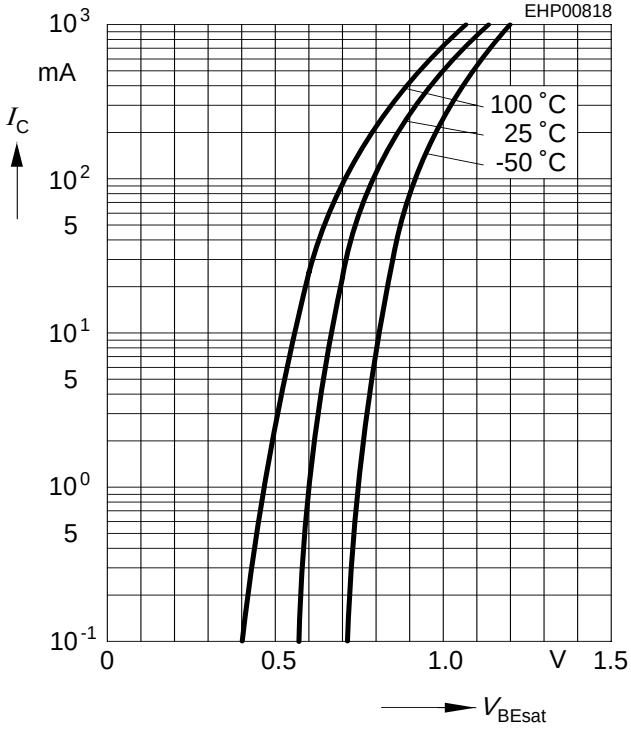
Collector-emitter saturation voltage

$I_C = f(V_{CEsat})$, h_{FE} = 10



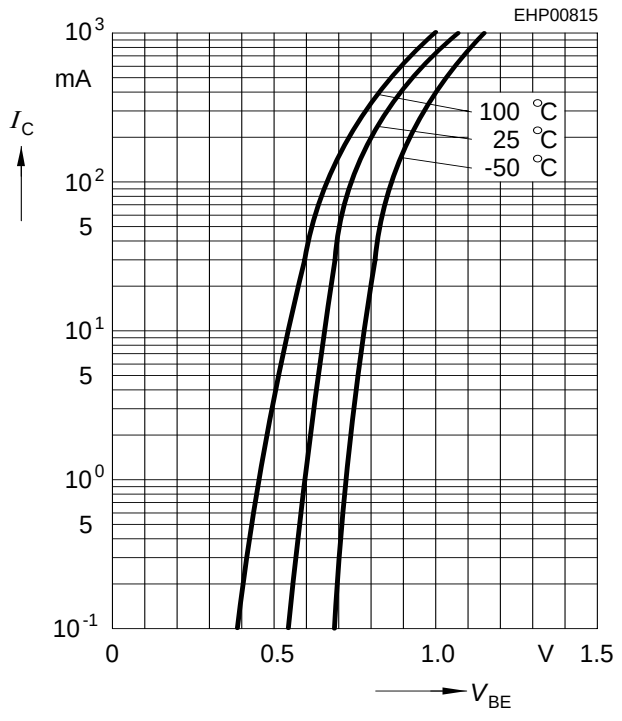
Base-emitter saturation voltage

$I_C = f(V_{BEsat})$, h_{FE} = 10



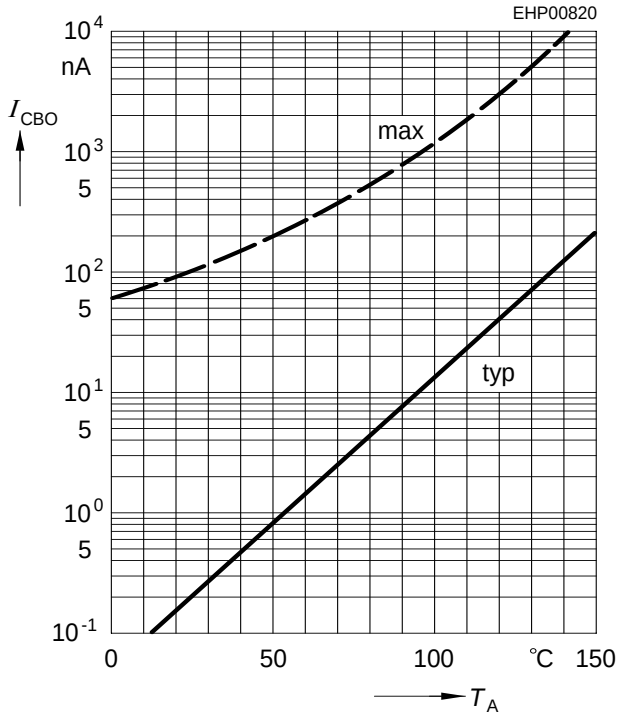
Collector current $I_C = f(V_{BE})$

V_{CE} = 1V



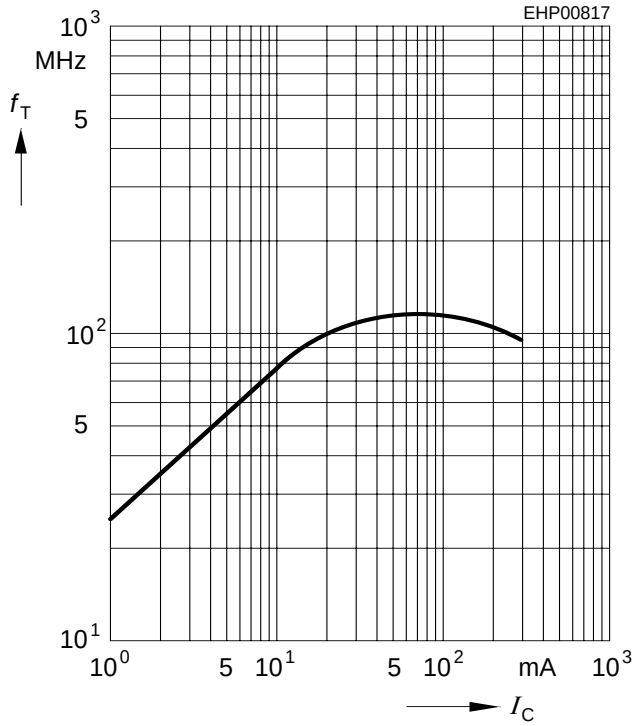
Collector cutoff current $I_{CBO} = f(T_A)$

V_{CBO} = 80 V



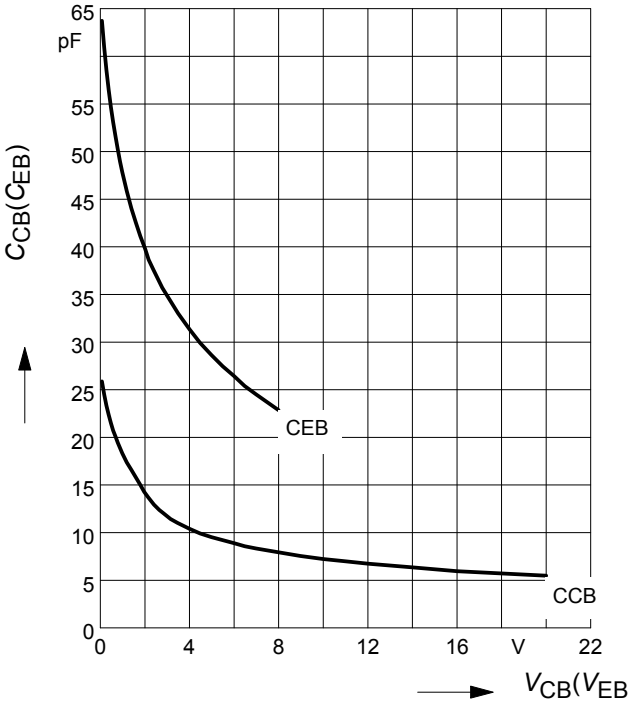
Transition frequency $f_T = f(I_C)$

V_{CE} = parameter in V, f = 2 GHz

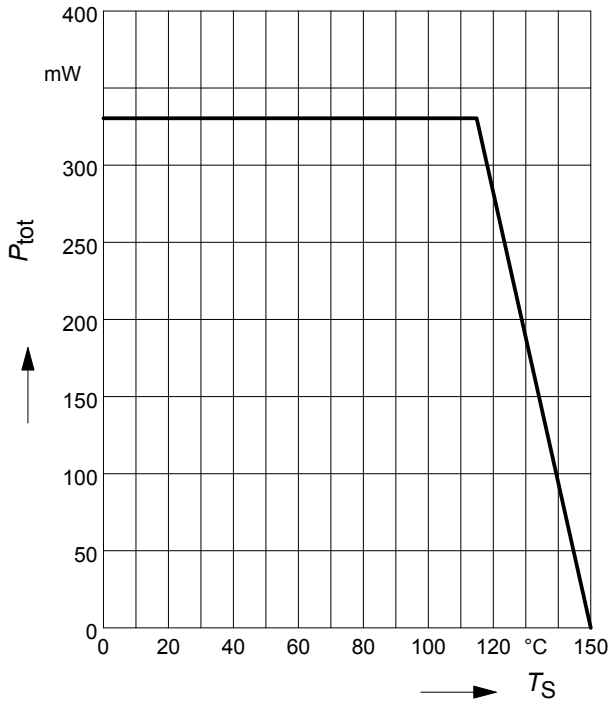


Collector-base capacitance $C_{cb} = f(V_{CB})$

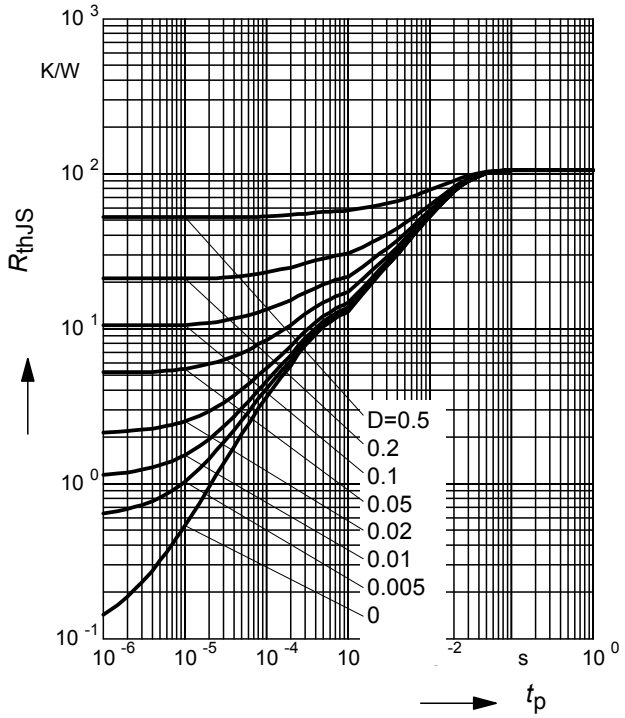
Emitter-base capacitance $C_{eb} = f(V_{EB})$



Total power dissipation $P_{tot} = f(T_S)$

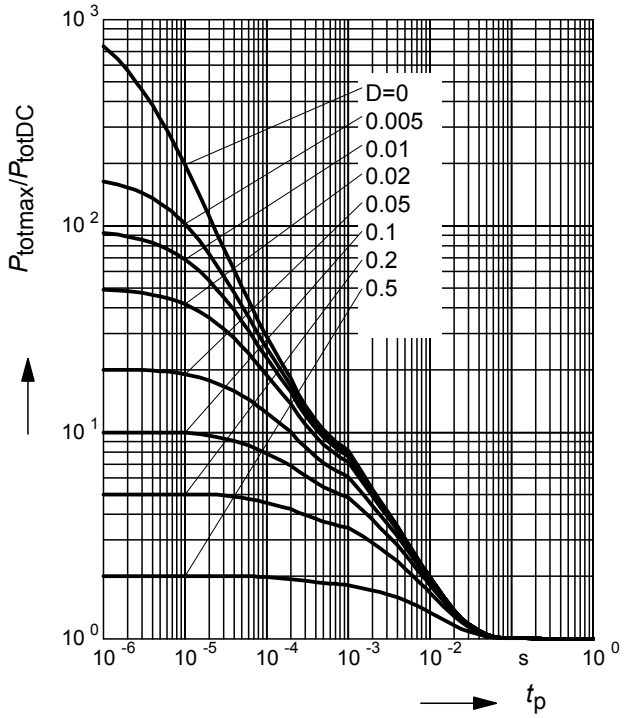


Permissible Pulse Load $R_{thJS} = f(t_p)$

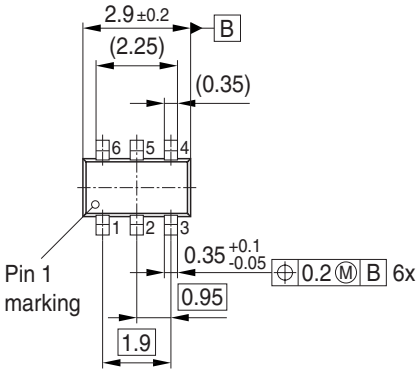


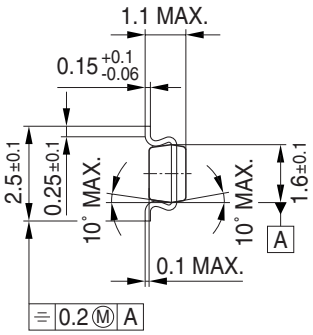
Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

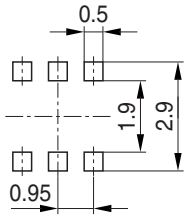


Package Outline



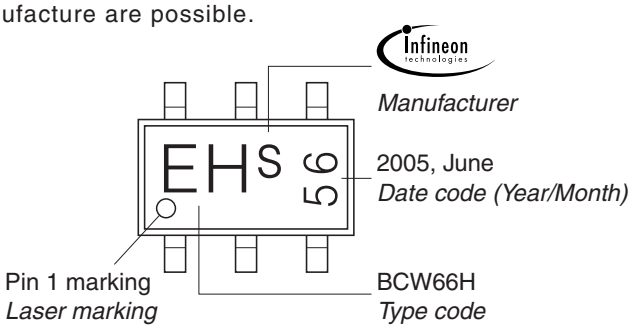


Foot Print



Marking Layout (Example)

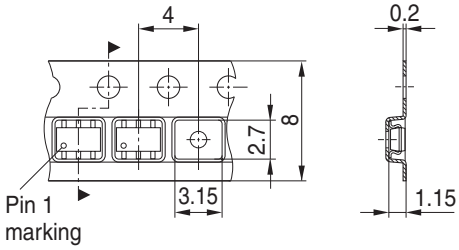
Small variations in positioning of
Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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